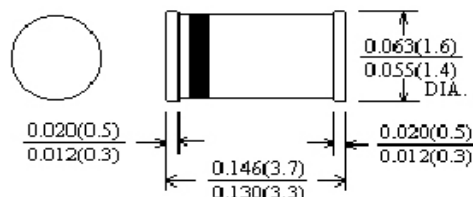


1N4150 mini-M.E.L.F. SIGNAL DIODE
MINI MELF (LL-34)
Mechanical Data

Items	Material
Package	mini MELF
Case	Hermetically sealed glass
Lead/Finish	Double stud/Tin Plating
Chip	Glass Passivated


Hermetically Sealed, Glass Silicon Diodes
Absolute Maximum Ratings (Ta=25 °C)

	Symbol	Value	UNIT
Reverse Voltage (continuous)	V_R	50	V
Power Dissipation at Tamb= 25 °C 3.33mW/ °C	P_{tot}	500	mW
Forward Current (DC)	I_F	300	mA
Average Rectified Output Current	I_O	200	mA
Repetitive Peak Forward Current	I_{FRM}	600	mA
Junction Temperature	T_j	-65 to +200	°C
Storage Temperature Range	T_S	-65 to +200	°C

Electrical Characteristics (Ta=25 °C)

	Symbol	Min	Max	Unit
Minimum Breakdown Voltage @ $I_R = 100\mu A$	BV	75	-	V
Peak Forward Surge Current PW<1 sec	I_{Fsurge}	-	500	mA
Maximum Forward Voltage $I_F = 200$ mA	V_F	-	1.0	V
Maximum reverse Leakage Current at $V_R = 50V$ at $V_R = 50V$, $T_j = 150$ °C	I_R	-	0.100 100	μA
Maximum Junction Capacitance $V_R = 0$, f= 1MHz	C_j	-	2.5	pF
Reverse Recovery Time $I_F = 10mA$ to $200mA$, $I_R = 10mA$ to $200mA$ $R_L = 100$ ohms Measured @ $I_R = 0.1I_F$	t_{rr}	-	4	ns
Forward Recovery Time Measured from $I=0$ to $I_F = 200mA$ $t_r = 0.4ns$, $t_p = 100ns$, Duty Cycle $\leq 1.0\%$ Measured @ $V_F = 1V$	t_{fr}	-	10	ns
Maximum Thermal Resistance Junction to Ambient Air	R_{thJA}	-	0.35	°C/mW